

Read Kindle

GAN-BASED HEMTS FOR HIGH VOLTAGE OPERATION: DESIGN, TECHNOLOGY AND CHARACTERIZATION



Cuvillier Verlag Jun 2012, 2012. Taschenbuch. Book Condition: Neu. 208x147x14 mm. Neuware - Gallium nitride (GaN)-based High Electron Mobility Transistors (HEMTs) for high voltage, high power switching and regulating for space applications are studied in this work. Efficient power switching is associated with operation in high OFF-state blocking voltage while keeping the ON-state resistance, the dynamic dispersion and leakage currents as low as possible. The potential of such devices to operate at high voltages is limited by a chain of...

Download PDF GaN-Based HEMTs for High Voltage Operation: Design, Technology and Characterization

- Authored by Eldad Bahat-Treidel
- Released at 2012



Filesize: 2.21 MB

Reviews

Great e-book and beneficial one. I am quite late in start reading this one, but better then never. You may like how the author publish this ebook.

-- **Mr. Alexandro Lemke MD**

It in a of the best publication. It really is rally intriguing throgh reading through period of time. You will not feel monotony at anytime of your own time (that's what catalogs are for relating to in the event you request me).

-- **Dr. Pat Hegmann**

Related Books

- [Psychologisches Testverfahren](#)
- [Programming in D](#)
- [Adobe Indesign CS/Cs2 Breakthroughs](#)
- [Readers Clubhouse B People on My Street](#)
- [In Nature s Realm, Op.91 / B.168: Study Score](#)